

## Boron Distributions in Individual Core-Shell Ge/Si and Si/Ge Heterostructured Nanowires

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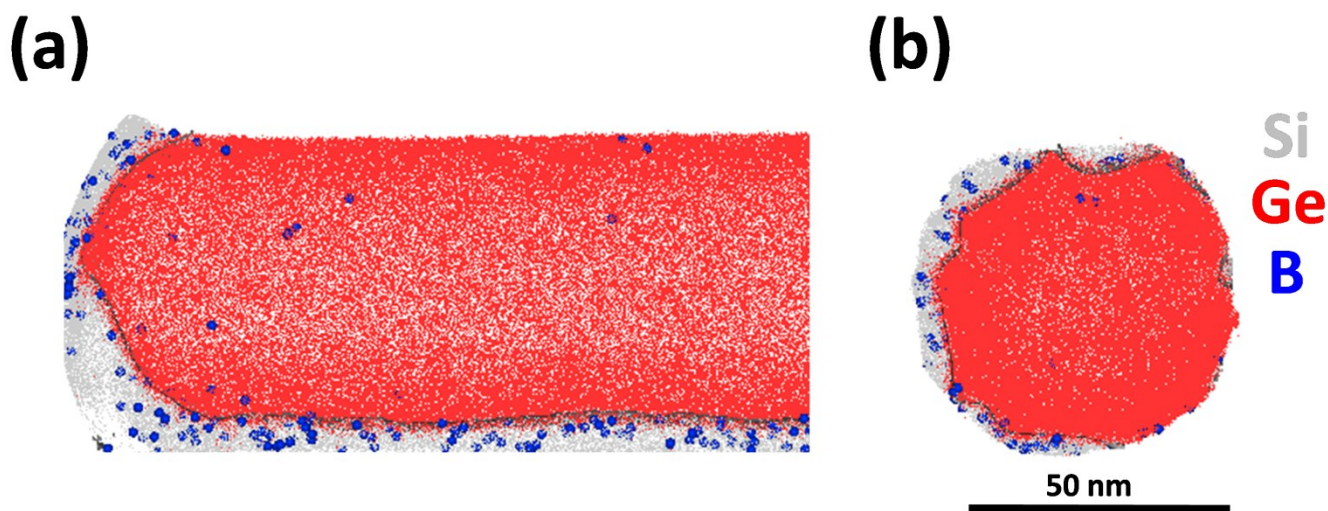
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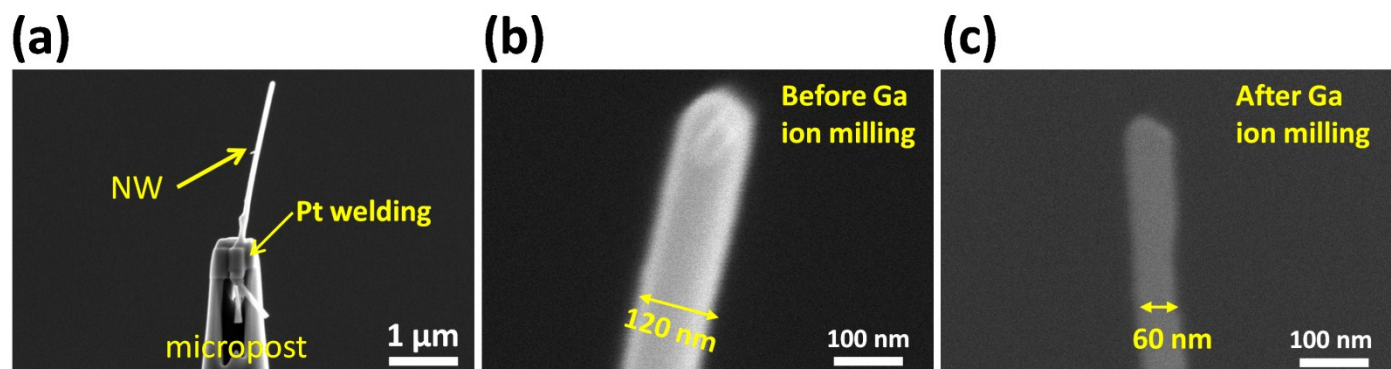
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### SUPPORTING INFORMATION

Additional figures:



**Fig. S1** Atom maps of a Ge/Si core-shell nanowire (NW) measured directly by APT without Ga ion milling. (a) side view and (b) top view of 10-nm-thick sliced atom maps. The 20 at.% Si iso-concentration surface is also shown. Due to the limited APT field-of-view, only a very thin Si shell could be detected.



**Fig. S2** In order to study the B distribution in the Si shells of Ge/Si core-shell NWs, NWs were milled by Ga focused ion beam (5 kV, 43 pA) before APT measurement. (a) a Ge/Si core-shell NW welded to a micropost. Top part of the NW (b) before and (c) after Ga ion milling.